FQD3N80

800V,2.8A N-Channel MOSFET

General Description

The FQD3N80 has been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.
By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability this part can be adopted quickly into new and existing offline power supply designs.

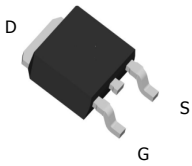
Product Summary

V_{DS}	900V@150℃
I_D (at V_{GS}=10V)	2.8A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.8Ω

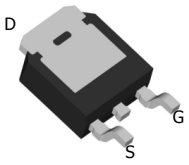
100% UIS Tested!
100% R_g Tested!

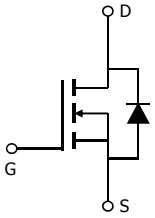
TO252
DPAK

Top View



Bottom View





Absolute Maximum Ratings T_A=25℃ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	800	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current[B]	T_C=25℃	I_D	2.8	A
	T_C=100℃		1.8	
Pulsed Drain Current [C]		I_{DM}	9	
Avalanche Current [C]		I_{AR}	2.2	A
Repetitive avalanche energy [C]		E_{AR}	72	mJ
Single pulsed avalanche energy [H]		E_{AS}	145	mJ
Peak diode recovery dv/dt		dv/dt	5	V/ns
Power Dissipation [B]	T_C=25℃	P_D	83	W
	Derate above 25°C		0.7	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-50 to 150	℃
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	℃

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A,G]	$R_{\theta JA}$	45	55	℃/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	-	0.5	℃/W
Maximum Junction-to-Case[D,F]	$R_{\theta JC}$	1.2	1.5	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V, T_J=25℃	800			V
		I_D=250μA, V_{GS}=0V, T_J=150℃		900		
BV_{DSS} /ΔTJ	Zero Gate Voltage Drain Current	ID=250μA, VGS=0V		0.78		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=800V, V_{GS}=0V			1	μA
		V_{DS}=640V, T_J=125℃			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250μA	3.3	4.2	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=1.5A		3.8	4.8	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=1.5A		2.5		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.77	1	V
I_S	Maximum Body-Diode Continuous Current				2.8	A
I_{SM}	Maximum Body-Diode Pulsed Current				9	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz		510		pF
C_{oss}	Output Capacitance			39		pF
C_{rss}	Reverse Transfer Capacitance			3.7		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		2.9		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=640V, I_D=3A		10		nC
Q_{gs}	Gate Source Charge			2.6		nC
Q_{gd}	Gate Drain Charge			2.9		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=400V, I_D=3A, R_G=25Ω		21		ns
t_r	Turn-On Rise Time			25		ns
$t_{D(off)}$	Turn-Off DelayTime			34		ns
t_f	Turn-Off Fall Time			19		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=3A,dI/dt=100A/μs,V_{DS}=100V		344		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=3A,dI/dt=100A/μs,V_{DS}=100V		2.2		μC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A=25° C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C.
G.These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.
H. L=60mH, I_{AS}=2.2A, V_{DD}=150V, R_G=10Ω, Starting T_J=25° C

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

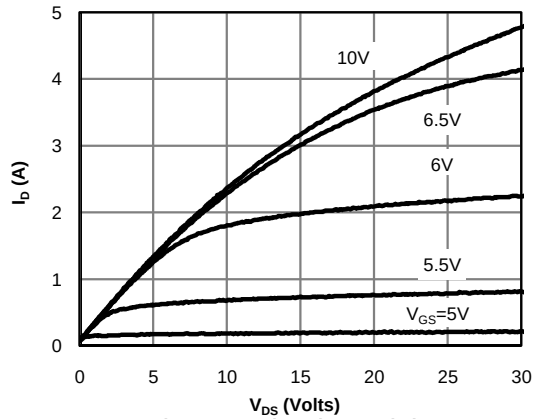


Fig 1: On-Region Characteristics

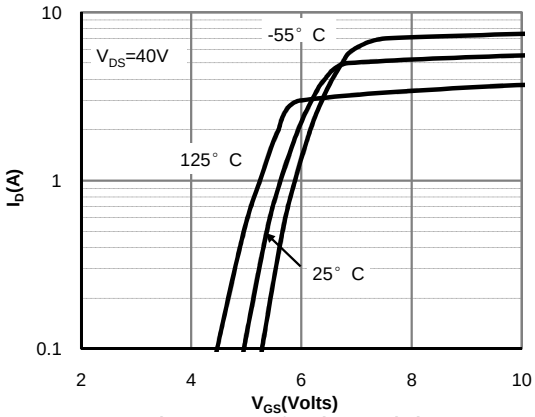


Figure 2: Transfer Characteristics

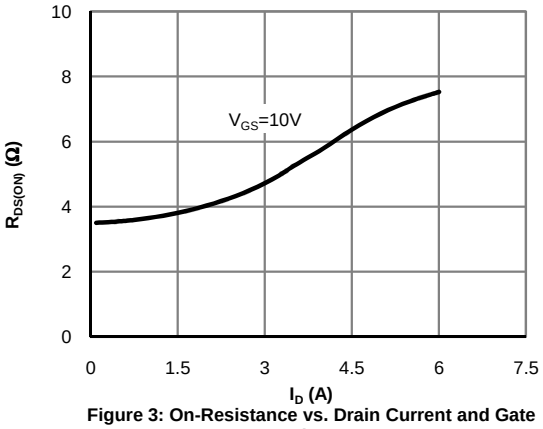


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

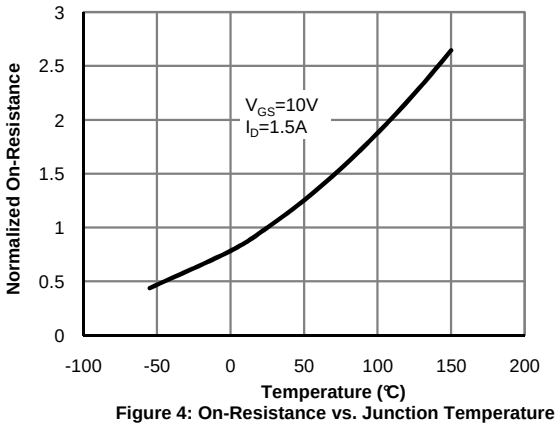


Figure 4: On-Resistance vs. Junction Temperature

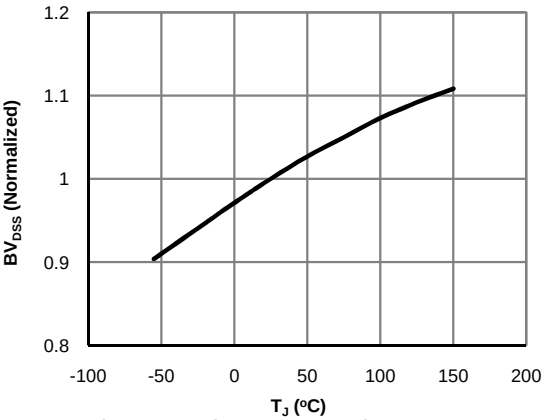


Figure 5: Break Down vs. Junction Temperature

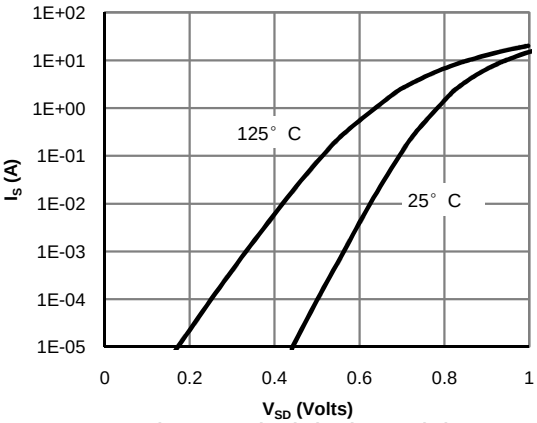


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

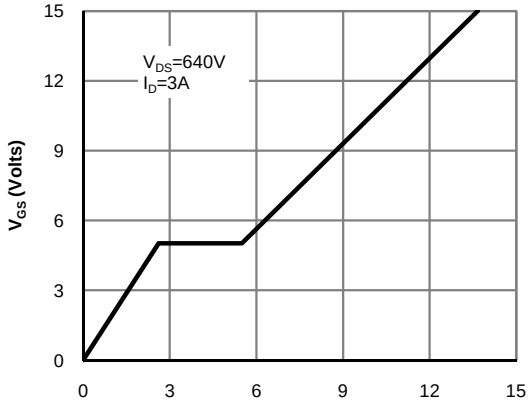


Figure 7: Gate-Charge Characteristics

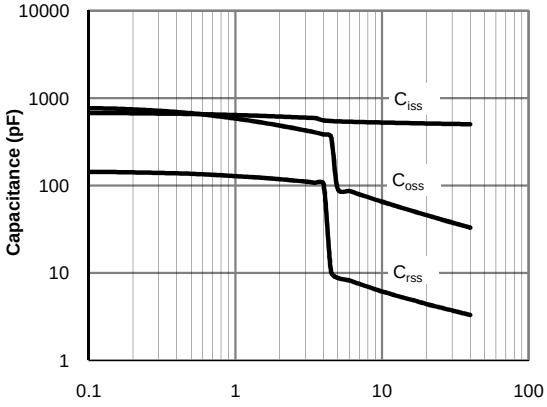


Figure 8: Capacitance Characteristics

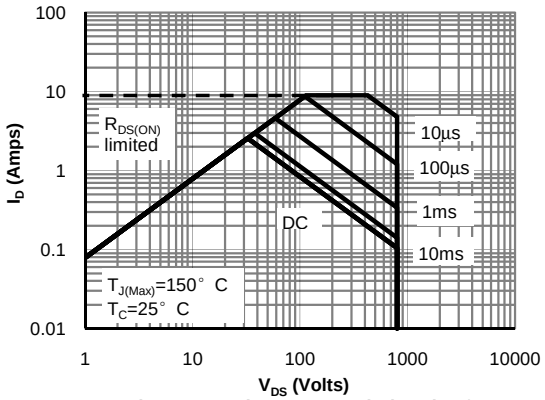


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

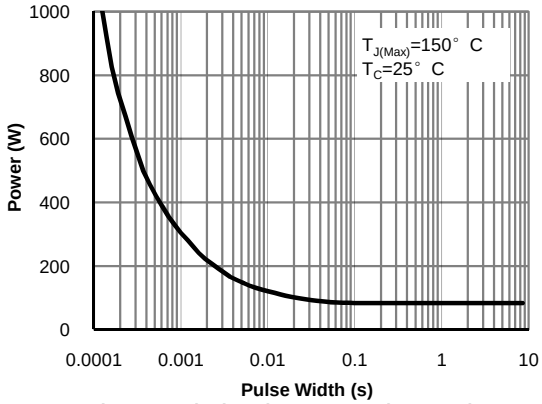


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

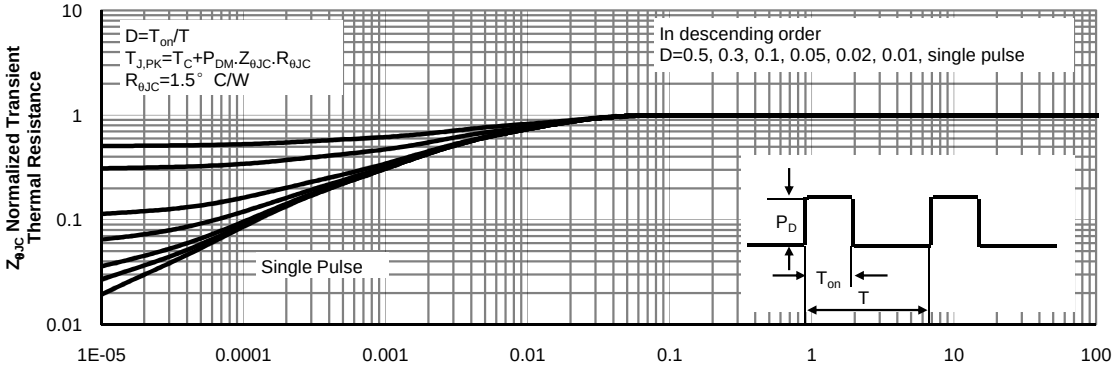


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

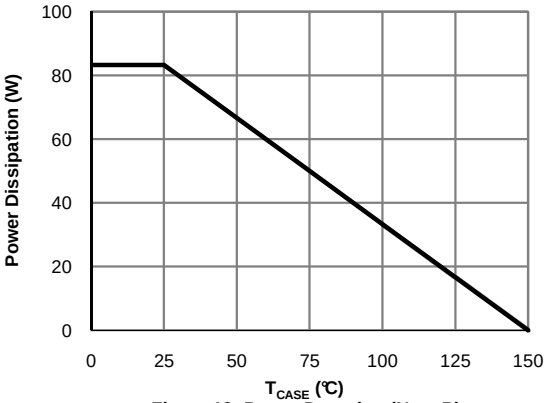


Figure 12: Power De-rating (Note B)

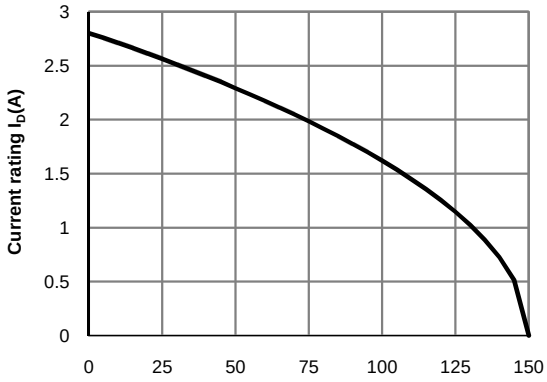


Figure 13: Current De-rating (Note B)

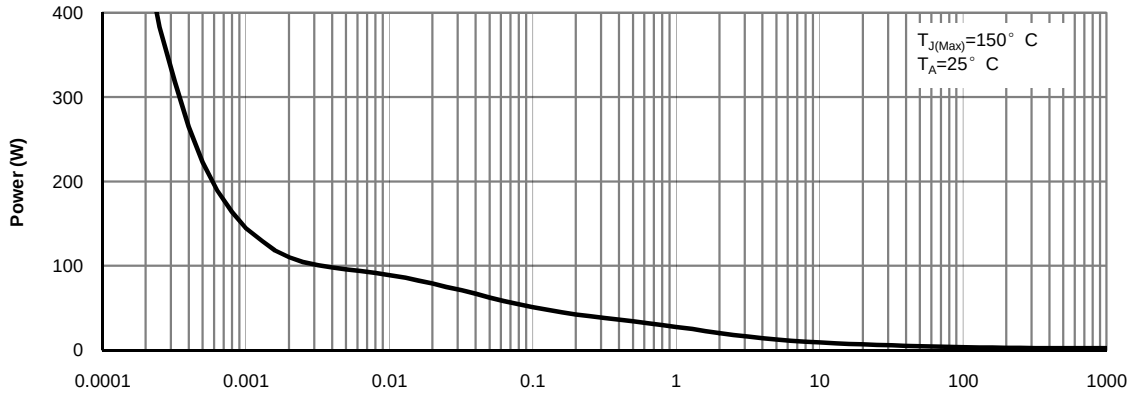


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

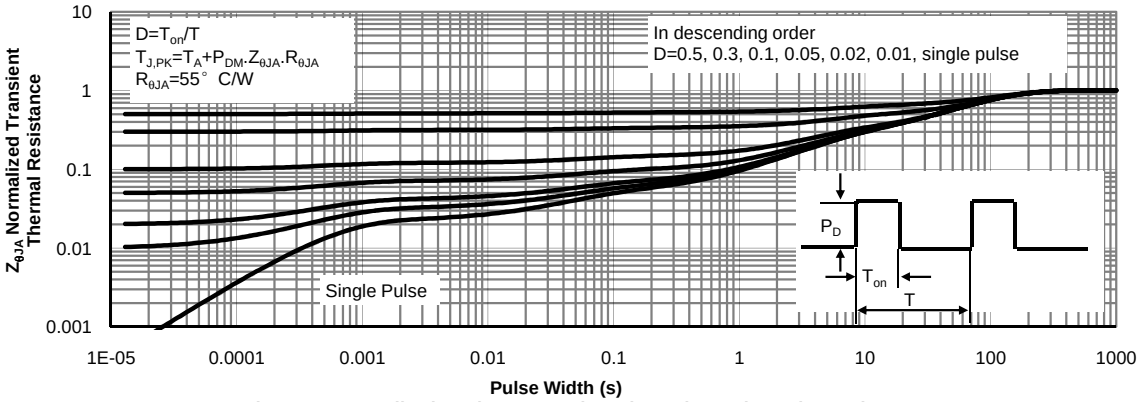
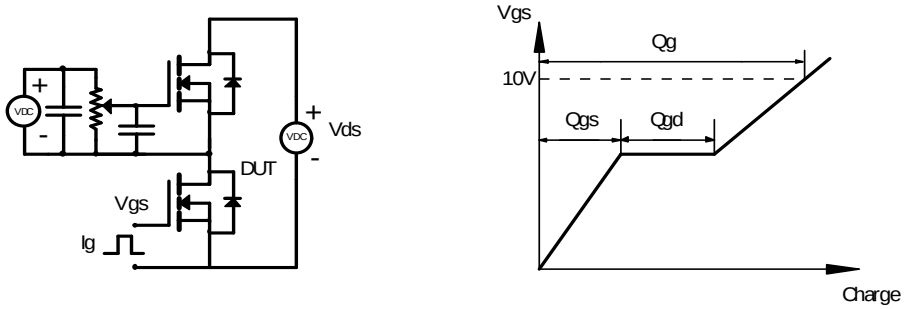
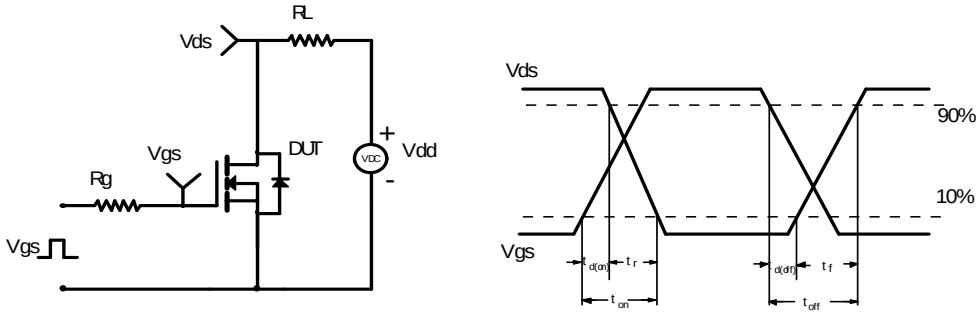


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

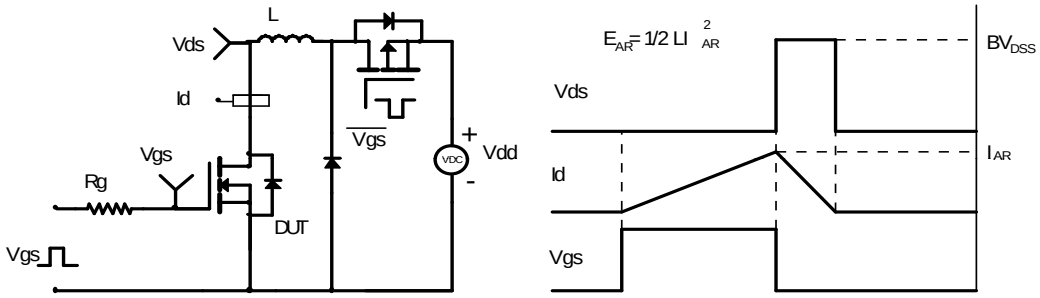
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms